

- MOVPE epi-wafer of InGaN alloy films
- Normal type chip (brightness enhanced with patterned substrate)
- ※ All samples are 100% tested and sorted, and user can consult about special specifications.

■ ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

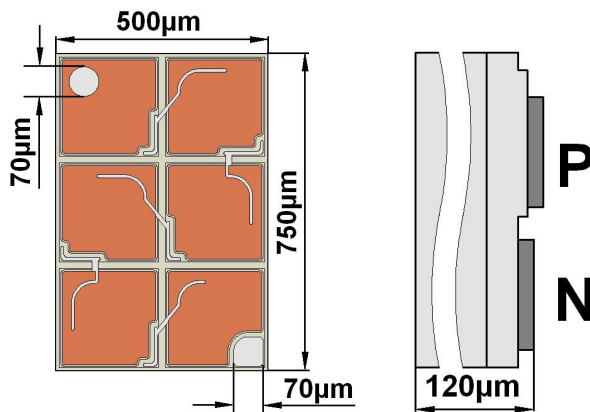
Item	Symbol	Maximum Rating	Unit
DC Forward Current	I _F	30	mA
Pulse Forward Current	I _{FP}	100	mA
Operating Temperature	T _{opr}	-30 to +85	°C
Storage Temperature	T _{stg}	-40 to +100	°C
ESD sensitivity (HBM) *	V _{ESDS}	2000	V

*2000V ESD testing result is based on statistic measurements and 500V ESD measurement is applied on full testing .

■ OPTICAL AND ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Item	Symbol	Condition		Min	Typ	Max	Unit
Forward Voltage	V _f	I _F =30mA	V ₁	18	-	19	V
			V ₂	19	-	20	
Reverse Current	I _R	V _R =60V		-	-	0.5	μA
Wavelength	λ _D	I _F =30mA	W ₁	450	-	452.5	nm
			W ₂	452.5	-	455	
			-	...	
			W ₄	457.5	-	460	
Optical power	p	I _F =30mA	-	...	mW
			P ₅	230	-	240	
			P ₆	240	-	250	
			P ₇	250	-	260	
			P ₈	260	-	270	
			-	...	

■ CHIP DESCRIPTION



■ MECHANICAL SPECIFICATION

Description	Dimension
Emission Area	480 μm x 725 μm
Bottom Area	500 μm x 750 μm (±10 μm)
Chip Thickness	120 μm (±5 μm)
N-pad	Φ=70 μm
P-pad	Φ=70 μm
Electrodes Spacing	10 μm
Electrode material	Al

